

Kazuhito Tsukagoshi

List of Publications by Year in descending order

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373
papers

14,180
citations

17405

63
h-index

28224

105
g-index

381
all docs

381
docs citations

381
times ranked

15196
citing authors

#	ARTICLE	IF	CITATIONS
1	C ₆₀ nanowire two-state resistance switching: fabrication and electrical characterizations. Japanese Journal of Applied Physics, 2022, 61, SD0804.	0.8	3
2	Principal Component Analysis of Surface-Enhanced Raman Scattering Spectra Revealing Isomer-Dependent Electron Transport in Spiropyran Molecular Junctions: Implications for Nanoscale Molecular Electronics. ACS Omega, 2022, 7, 5578-5583.	1.6	15
3	Non-invasive digital etching of van der Waals semiconductors. Nature Communications, 2022, 13, 1844.	5.8	8
4	Operando hard X-ray photoelectron spectroscopy study of buried interface chemistry of Au/InO _{1.16} C _{0.04} /Al ₂ O ₃ /p<math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e383" altimg="si20.svg">$+$-Si stacks. Applied Surface Science, 2022, 593, 153272.	3.1	1
5	Fullerene Nanostructure-Coated Channels Activated by Electron Beam Lithography for Resistance Switching. ACS Applied Nano Materials, 2022, 5, 6430-6437.	2.4	3
6	Fullerene C ₇₀ /porphyrin hybrid nanoarchitectures: single-cocrystal nanoribbons with ambipolar charge transport properties. RSC Advances, 2022, 12, 19548-19553.	1.7	2
7	Nanoarchitectonics of C70 hexagonal nanosheets: Synthesis and charge transport properties. Diamond and Related Materials, 2022, 128, 109217.	1.8	6
8	C ₆₀ -Nanowire Two-State Resistance Switching Based on Fullerene Polymerization/Depolymerization. ACS Applied Nano Materials, 2021, 4, 820-825.	2.4	12
9	Comparison of characteristics of thin-film transistor with In ₂ O ₃ and carbon-doped In ₂ O ₃ channels by atomic layer deposition and post-metallization annealing in O ₃ . Japanese Journal of Applied Physics, 2021, 60, 030903.	0.8	6
10	Influence of adsorbed oxygen concentration on characteristics of carbon-doped indium oxide thin-film transistors under bias stress. Japanese Journal of Applied Physics, 2021, 60, SCCM01.	0.8	3
11	Determination of Chemical Structure of Bis(dithiolato)iron Nanosheet. Chemistry Letters, 2021, 50, 576-579.	0.7	10
12	Tunable Doping of Rhenium and Vanadium into Transition Metal Dichalcogenides for Two-Dimensional Electronics. Advanced Science, 2021, 8, e2004438.	5.6	66
13	Fabrication of WO ₃ electrochromic devices using electro-exploding wire techniques and spray coating. Solar Energy Materials and Solar Cells, 2021, 223, 110960.	3.0	45
14	Two-Dimensional Bis(dithiolene)iron(II) Self-Powered UV Photodetectors with Ultrahigh Air Stability. Advanced Science, 2021, 8, 2100564.	5.6	19
15	Water Splitting Induced by Visible Light at a Copper-Based Single-Molecule Junction. Small, 2021, 17, e2008109.	5.2	3
16	Water Splitting: Water Splitting Induced by Visible Light at a Copper-Based Single-Molecule Junction (Small 28/2021). Small, 2021, 17, 2170143.	5.2	0
17	C ₆₀ -Nanowire Two-State Resistance Switching. Journal of Japan Institute of Electronics Packaging, 2021, 24, 401-409.	0.0	0
18	Stable Resistance Switching in Lu ₃ N@C ₈₀ Nanowires Promoted by the Endohedral Effect: Implications for Single-Fullerene Motion Resistance Switching. ACS Applied Nano Materials, 2021, 4, 7935-7942.	2.4	7

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19	Splitting charge injection for ultrahigh on/off ratio in a floating-metal-gated planar organic ferroelectric memory. <i>Materials Today Energy</i> , 2021, 21, 100711.	2.5	6
20	Mixed-Salt Enhanced Chemical Vapor Deposition of Two-Dimensional Transition Metal Dichalcogenides. <i>Chemistry of Materials</i> , 2021, 33, 7301-7308.	3.2	22
21	(Invited) Study of HfO ₂ -Based High-k Gate Insulators for GaN Power Device. <i>ECS Transactions</i> , 2021, 104, 113-120.	0.3	2
22	Importance of Annealing Step on Dielectric Constant of ZrO ₂ Layer of MIM Capacitors with Al ₂ O ₃ /ZrO ₂ and ZrO ₂ /Al ₂ O ₃ Stack Structures. <i>ECS Transactions</i> , 2021, 104, 121-128.	0.3	1
23	Visualizing band alignment across 2D/3D perovskite heterointerfaces of solar cells with light-modulated scanning tunneling microscopy. <i>Nano Energy</i> , 2021, 89, 106362.	8.2	13
24	Surface-Enhanced Raman Scattering Stimulated by Strong Metal-Molecule Interactions in a C ₆₀ Single-Molecule Junction. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 51602-51607.	4.0	9
25	Solution-processed organic single-crystalline semiconductors with a fence-like shape <i>via</i> ultrasound concussion. <i>Journal of Materials Chemistry C</i> , 2020, 8, 2589-2593.	2.7	2
26	One-Dimensional Fullerene/Porphyrin Cocrystals: Near-Infrared Light Sensing through Component Interactions. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 2878-2883.	4.0	21
27	Unravelling the origin of the photocarrier dynamics of fullerene-derivative passivation of SnO ₂ electron transporters in perovskite solar cells. <i>Journal of Materials Chemistry A</i> , 2020, 8, 23607-23616.	5.2	30
28	Facile and Reversible Carrier-Type Manipulation of Layered MoTe ₂ Toward Long-Term Stable Electronics. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 42918-42924.	4.0	4
29	Quantum-assisted photoelectric gain effects in perovskite solar cells. <i>NPG Asia Materials</i> , 2020, 12, .	3.8	12
30	Ab-initio investigation of preferential triangular self-formation of oxide heterostructures of monolayer WSe_2 . <i>Scientific Reports</i> , 2020, 10, 21737.	1.6	1
31	On/Off Boundary of Photocatalytic Activity between Single- and Bilayer MoS ₂ . <i>ACS Nano</i> , 2020, 14, 6663-6672.	7.3	29
32	Solution-processed organometallic quasi-two-dimensional nanosheets as a hole buffer layer for organic light-emitting devices. <i>Nanoscale</i> , 2020, 12, 6983-6990.	2.8	14
33	Feedback Electromigration Assisted by Alternative Voltage Operation for the Fabrication of Facet-Edge Nanogap Electrodes. <i>ACS Applied Nano Materials</i> , 2020, 3, 4077-4083.	2.4	11
34	Tolerance to Stretching in Thiol-Terminated Single-Molecule Junctions Characterized by Surface-Enhanced Raman Scattering. <i>Journal of Physical Chemistry Letters</i> , 2020, 11, 6712-6717.	2.1	15
35	Solution processed In-Si-O thin film transistors on hydrophilic and hydrophobic substrates. <i>Thin Solid Films</i> , 2020, 698, 137860.	0.8	5
36	Measurement of the Low-Energy Electron Inelastic Mean Free Path in Monolayer Graphene. <i>Physical Review Applied</i> , 2020, 13, .	1.5	10

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37	UV degradation mechanism of TiO ₂ -based perovskite solar cells studied by pump-probe spectroscopy. , 2020, , .		7
38	Wafer-scale and deterministic patterned growth of monolayer MoS ₂ via liquid-solid method. Nanoscale, 2019, 11, 16122-16129.	2.8	76
39	Investigation of Ag and Cu Filament Formation Inside the Metal Sulfide Layer of an Atomic Switch Based on Point-Contact Spectroscopy. ACS Applied Materials & Interfaces, 2019, 11, 27178-27182.	4.0	9
40	Suppression of threshold voltage shift on In-Si-O-C Thin-Film Transistor with an Al ₂ O ₃ Passivation Layer under Negative and Positive Gate-Bias Stress. , 2019, , .		0
41	Observation of Plasmon Energy Gain for Emitted Secondary Electron in Vacuo. Journal of Physical Chemistry Letters, 2019, 10, 5770-5775.	2.1	8
42	Tunable Chemical Coupling in Two-Dimensional van der Waals Electrostatic Heterostructures. ACS Nano, 2019, 13, 11214-11223.	7.3	13
43	Si-incorporated amorphous indium oxide thin-film transistors. Japanese Journal of Applied Physics, 2019, 58, 090506.	0.8	16
44	Origin of Extended UV Stability of 2D Atomic Layer Titania-Based Perovskite Solar Cells Unveiled by Ultrafast Spectroscopy. ACS Applied Materials & Interfaces, 2019, 11, 21473-21480.	4.0	11
45	Effect of Bias Voltage on a Single-Molecule Junction Investigated by Surface-Enhanced Raman Scattering. Journal of Physical Chemistry C, 2019, 123, 15267-15272.	1.5	6
46	Identifying the molecular adsorption site of a single molecule junction through combined Raman and conductance studies. Chemical Science, 2019, 10, 6261-6269.	3.7	32
47	Stretch dependent electronic structure and vibrational energy of the bipyridine single molecule junction. Physical Chemistry Chemical Physics, 2019, 21, 16910-16913.	1.3	7
48	Near-infrared-light-induced decomposition of Rhodamine B triggered by localized surface plasmon at gold square dimers with well-defined separation distance. AIP Advances, 2019, 9, .	0.6	1
49	Silicon-doped indium oxide a promising amorphous oxide semiconductor material for thin-film transistor fabricated by spin coating method. IOP Conference Series: Materials Science and Engineering, 2019, 625, 012002.	0.3	2
50	Oxygen-Sensitive Layered MoTe ₂ Channels for Environmental Detection. ACS Applied Materials & Interfaces, 2019, 11, 47047-47053.	4.0	13
51	Selective oxidation of the surface layer of bilayer WSe ₂ by laser heating. Japanese Journal of Applied Physics, 2019, 58, 120903.	0.8	6
52	Characteristics of Oxide TFT Using Carbon-Doped In ₂ O ₃ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (In-EtCp) and H ₂ O. ECS Transactions, 2019, 92, 3-13.	0.3	17
53	Si-doping effect on solution-processed In-O thin-film transistors. Materials Research Express, 2019, 6, 026410.	0.8	2
54	Reversible and Precisely Controllable p/n-Type Doping of MoTe ₂ Transistors through Electrothermal Doping. Advanced Materials, 2018, 30, e1706995.	11.1	68

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55	Unveiling the piezoelectric nature of polar $\hat{\pm}$ -phase P(VDF-TrFE) at quasi-two-dimensional limit. <i>Scientific Reports</i> , 2018, 8, 532.	1.6	14
56	Carrier polarity engineering in carbon nanotube field-effect transistors by induced charges in polymer insulator. <i>Applied Physics Letters</i> , 2018, 112, 013501.	1.5	12
57	Pronounced photogating effect in atomically thin WSe ₂ with a self-limiting surface oxide layer. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	38
58	Fullerene/cobalt porphyrin charge-transfer cocrystals: Excellent thermal stability and high mobility. <i>Nano Research</i> , 2018, 11, 1917-1927.	5.8	27
59	Self-Assembly Atomic Stacking Transport Layer of 2D Layered Titania for Perovskite Solar Cells with Extended UV Stability. <i>Advanced Energy Materials</i> , 2018, 8, 1701722.	10.2	46
60	Reliability of Al ₂ O ₃ /In-Si-O-C Thin-Film Transistors with an Al ₂ O ₃ Passivation Layer under Gate-Bias Stress. <i>ECS Transactions</i> , 2018, 86, 135-145.	0.3	4
61	Thermal robustness evaluation of nonvolatile memory using Pt nanogaps. <i>Applied Physics Express</i> , 2018, 11, 085202.	1.1	3
62	Investigation on solution-processed In-Si-O thin-film transistor via spin-coating method. , 2018, , .		1
63	Solvent-Mediated Shape Engineering of Fullerene (C ₆₀) Polyhedral Microcrystals. <i>Chemistry of Materials</i> , 2018, 30, 7146-7153.	3.2	37
64	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018, 36, 061206.	0.6	5
65	Dependence of Stretch Length on Electrical Conductance and Electronic Structure of the Benzenedithiol Single Molecular Junction. <i>E-Journal of Surface Science and Nanotechnology</i> , 2018, 16, 145-149.	0.1	2
66	Layer-by-Layer Oxidation Induced Electronic Properties in Transition-Metal Dichalcogenides. <i>Journal of Physical Chemistry C</i> , 2018, 122, 17001-17007.	1.5	12
67	Photochemical Reaction Using Aminobenzenethiol Single Molecular Junction. <i>E-Journal of Surface Science and Nanotechnology</i> , 2018, 16, 137-141.	0.1	2
68	<i>In situ</i> observation of the formation process for free-standing Au nanowires with a scanning electron microscope. <i>Nanotechnology</i> , 2017, 28, 105707.	1.3	2
69	Amorphous In-Si-O Films Fabricated via Solution Processing. <i>Journal of Electronic Materials</i> , 2017, 46, 3610-3614.	1.0	7
70	Virtual substrate method for nanomaterials characterization. <i>Nature Communications</i> , 2017, 8, 15629.	5.8	25
71	Correlation between active layer thickness and ambient gas stability in IGZO thin-film transistors. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 025102.	1.3	4
72	Controlling the thermoelectric effect by mechanical manipulation of the electron's quantum phase in atomic junctions. <i>Scientific Reports</i> , 2017, 7, 7949.	1.6	12

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73	Flexible and Printed Electronics. Japanese Journal of Applied Physics, 2017, 56, 05E001.	0.8	1
74	Radial Interference Contrast in in-situ SEM Observation of Metal Oxide Semiconductor Film Crystallization. Microscopy and Microanalysis, 2017, 23, 1512-1513.	0.2	1
75	Gap width-independent spectra in 4-aminothiophenol surface enhanced Raman scattering stimulated in Au-gap array. Japanese Journal of Applied Physics, 2017, 56, 065202.	0.8	3
76	Self-powered graphene thermistor. Nano Energy, 2016, 26, 586-594.	8.2	27
77	Phase transitions from semiconductive amorphous to conductive polycrystalline in indium silicon oxide thin films. Applied Physics Letters, 2016, 109, .	1.5	13
78	Anomalous behavior of $1/f$ noise in graphene near the charge neutrality point. Applied Physics Letters, 2016, 108, .	1.5	11
79	Homogeneous double-layer amorphous Si-doped indium oxide thin-film transistors for control of turn-on voltage. Journal of Applied Physics, 2016, 120, .	1.1	19
80	Carrier Polarity Control in In_2MoTe_2 Schottky Junctions Based on Weak Fermi-Level Pinning. ACS Applied Materials & Interfaces, 2016, 8, 14732-14739.	4.0	72
81	Prospectively of Carbon-Doped Indium-Tungsten-Oxide Channel TFT for Bias Stress Instability. ECS Transactions, 2016, 75, 149-156.	0.3	5
82	Two-dimensional MoTe_2 materials: From synthesis, identification, and charge transport to electronics applications. Japanese Journal of Applied Physics, 2016, 55, 1102A1.	0.8	20
83	High-performance non-volatile field-effect transistor memories using an amorphous oxide semiconductor and ferroelectric polymer. Journal of Materials Chemistry C, 2016, 4, 7917-7923.	2.7	15
84	Highly stable, extremely high-temperature, nonvolatile memory based on resistance switching in polycrystalline Pt nanogaps. Scientific Reports, 2016, 6, 34961.	1.6	12
85	Hunting for Monolayer Oxide Nanosheets and Their Architectures. Scientific Reports, 2016, 6, 19402.	1.6	23
86	Determination of the number of atoms present in nano contact based on shot noise measurements with highly stable nano-fabricated electrodes. Nanotechnology, 2016, 27, 295203.	1.3	2
87	Self-Limiting Oxides on WSe_2 as Controlled Surface Acceptors and Low-Resistance Hole Contacts. Nano Letters, 2016, 16, 2720-2727.	4.5	131
88	Improvement of the effective work function and transmittance of thick indium tin oxide/ultrathin ruthenium doped indium oxide bilayers as transparent conductive oxide. Thin Solid Films, 2016, 598, 126-130.	0.8	3
89	Site-Selection in Single-Molecule Junction for Highly Reproducible Molecular Electronics. Journal of the American Chemical Society, 2016, 138, 1294-1300.	6.6	88
90	Charge transport and mobility engineering in two-dimensional transition metal chalcogenide semiconductors. Chemical Society Reviews, 2016, 45, 118-151.	18.7	423

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91	Nanocontact Disorder in Nanoelectronics for Modulation of Light and Gas Sensitivities. Scientific Reports, 2015, 5, 13035.	1.6	9
92	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. Journal of Applied Physics, 2015, 118, .	1.1	23
93	Influence of Al ₂ O ₃ layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	6
94	Reducing contact resistance in ferroelectric organic transistors by buffering the semiconductor/dielectric interface. Applied Physics Letters, 2015, 107, .	1.5	21
95	Origin of Noise in Layered MoTe ₂ Transistors and its Possible Use for Environmental Sensors. Advanced Materials, 2015, 27, 6612-6619.	11.1	72
96	Electrostatically Reversible Polarity of Ambipolar $\bar{1}\pm$ -MoTe ₂ Transistors. ACS Nano, 2015, 9, 5976-5983.	7.3	113
97	Epitaxial CVD growth of high-quality graphene and recent development of 2D heterostructures. , 2015, , .		0
98	Wafer-scale fabrication of transistors using CVD-grown graphene and its application to inverter circuit. Japanese Journal of Applied Physics, 2015, 54, 04DN06.	0.8	6
99	Self-Limiting Layer-by-Layer Oxidation of Atomically Thin WSe ₂ . Nano Letters, 2015, 15, 2067-2073.	4.5	204
100	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. Applied Physics Letters, 2015, 106, .	1.5	56
101	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. Applied Physics Letters, 2015, 106, .	1.5	25
102	Parity effect of bipolar quantum Hall edge transport around graphene antidots. Scientific Reports, 2015, 5, 11723.	1.6	7
103	Double resonance Raman modes in monolayer and few-layer $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:mi mathvariant="normal"} \rangle \text{MoTe} \langle \text{mml:mi} \rangle \langle \text{mml:mn} \rangle 2 \langle \text{mml:mn} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:math} \rangle$. Physical Review B. 2015, 91, .	1.1	99
104	Edge mixing dynamics in graphene p \bar{e} n junctions in the quantum Hall regime. Nature Communications, 2015, 6, 8066.	5.8	28
105	Reduction of the interfacial trap density of indium-oxide thin film transistors by incorporation of hafnium and annealing process. AIP Advances, 2015, 5, .	0.6	16
106	Carrier Injection and Scattering in Atomically Thin Chalcogenides. Journal of the Physical Society of Japan, 2015, 84, 121011.	0.7	7
107	Solution-assembled nanowires for high performance flexible and transparent solar-blind photodetectors. Journal of Materials Chemistry C, 2015, 3, 596-600.	2.7	45
108	Impact of Carbon-Doped $\bar{1}\frac{1}{4}$ n-Si-O Channel for Future TFT. ECS Meeting Abstracts, 2015, , .	0.0	0

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109	Influence of Al ₂ O ₃ Gate Dielectric on Transistor Properties for IGZO Thin Film Transistor. ECS Transactions, 2014, 61, 345-351.	0.3	2
110	Stable amorphous In ₂ O ₃ -based thin-film transistors by incorporating SiO ₂ to suppress oxygen vacancies. Applied Physics Letters, 2014, 104, .	1.5	83
111	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. Applied Physics Letters, 2014, 104, 152103.	1.5	79
112	Modulation of effective damping constant using spin Hall effect. Applied Physics Letters, 2014, 104, 092408.	1.5	37
113	Controllable film densification and interface flatness for high-performance amorphous indium oxide based thin film transistors. Applied Physics Letters, 2014, 105, .	1.5	9
114	Spin injection and detection in a graphene lateral spin valve using an yttrium-oxide tunneling barrier. Applied Physics Express, 2014, 7, 085101.	1.1	6
115	Self-formed copper oxide contact interlayer for high-performance oxide thin film transistors. Applied Physics Letters, 2014, 105, .	1.5	13
116	Ambipolar MoTe ₂ Transistors and Their Applications in Logic Circuits. Advanced Materials, 2014, 26, 3263-3269.	11.1	388
117	Thickness Scaling Effect on Interfacial Barrier and Electrical Contact to Two-Dimensional MoS ₂ Layers. ACS Nano, 2014, 8, 12836-12842.	7.3	149
118	Large [6,6]-phenyl C61 butyric acid methyl (PCBM) hexagonal crystals grown by solvent-vapor annealing. Materials Chemistry and Physics, 2014, 145, 327-333.	2.0	13
119	Control of molecular orientation and morphology in organic bilayer solar cells: Copper phthalocyanine on gold nanodots. Thin Solid Films, 2014, 562, 467-470.	0.8	9
120	Patterning technology for solution-processed organic crystal field-effect transistors. Science and Technology of Advanced Materials, 2014, 15, 024203.	2.8	39
121	Highly stable Au atomic contacts covered with benzenedithiol under ambient conditions. Physical Chemistry Chemical Physics, 2014, 16, 15662.	1.3	10
122	Barrier inhomogeneities at vertically stacked graphene-based heterostructures. Nanoscale, 2014, 6, 795-799.	2.8	64
123	Electrostatically Reversible Polarity of Dual-Gated Graphene Transistors. IEEE Nanotechnology Magazine, 2014, 13, 1039-1043.	1.1	14
124	Semiconducting properties of bilayer graphene modulated by an electric field for next-generation atomic-film electronics. Journal Physics D: Applied Physics, 2014, 47, 094003.	1.3	7
125	Strong Enhancement of Raman Scattering from a Bulk-Inactive Vibrational Mode in Few-Layer MoTe ₂ . ACS Nano, 2014, 8, 3895-3903.	7.3	275
126	Structure and transport properties of the interface between CVD-grown graphene domains. Nanoscale, 2014, 6, 7288.	2.8	52

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127	Strain-Tunable Superconducting Field-Effect Transistor with an Organic Strongly-Correlated Electron System. <i>Advanced Materials</i> , 2014, 26, 3490-3495.	11.1	29
128	Boost Up Carrier Mobility for Ferroelectric Organic Transistor Memory via Buffering Interfacial Polarization Fluctuation. <i>Scientific Reports</i> , 2014, 4, 7227.	1.6	67
129	Metal atomic contacts under defined environmental conditions. <i>Transactions of the Materials Research Society of Japan</i> , 2014, 39, 225-229.	0.2	0
130	Thickness-Dependent Interfacial Coulomb Scattering in Atomically Thin Field-Effect Transistors. <i>Nano Letters</i> , 2013, 13, 3546-3552.	4.5	285
131	Rational design of a high performance all solid state flexible micro-supercapacitor on paper. <i>RSC Advances</i> , 2013, 3, 15827.	1.7	45
132	Low-Cost Fully Transparent Ultraviolet Photodetectors Based on Electrospun ZnO/SnO ₂ Heterojunction Nanofibers. <i>Advanced Materials</i> , 2013, 25, 4625-4630.	11.1	275
133	High-performance top-gated monolayer SnS ₂ field-effect transistors and their integrated logic circuits. <i>Nanoscale</i> , 2013, 5, 9666.	2.8	269
134	On Practical Charge Injection at the Metal/Organic Semiconductor Interface. <i>Scientific Reports</i> , 2013, 3, 1026.	1.6	71
135	Suppression of thermally activated carrier transport in atomically thin MoS ₂ on crystalline hexagonal boron nitride substrates. <i>Nanoscale</i> , 2013, 5, 9572.	2.8	69
136	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. <i>Applied Physics Express</i> , 2013, 6, 075101.	1.1	83
137	Self-Aligned Formation of Sub 1 nm Gaps Utilizing Electromigration during Metal Deposition. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 12869-12875.	4.0	23
138	Self-assembly of semiconductor/insulator interfaces in one-step spin-coating: a versatile approach for organic field-effect transistors. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 7917.	1.3	59
139	Realization of graphene field-effect transistor with high- ϵ HfCa ₂ Nb ₃ O ₁₀ nanoflake as top-gate dielectric. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	12
140	Understanding Thickness-Dependent Charge Transport in Pentacene Transistors by Low-Frequency Noise. <i>IEEE Electron Device Letters</i> , 2013, 34, 1298-1300.	2.2	19
141	Flexible SnO ₂ hollow nanosphere film based high-performance ultraviolet photodetector. <i>Chemical Communications</i> , 2013, 49, 3739.	2.2	93
142	Structural and charge transport characteristics of graphene layers obtained from CVD thin film and bulk graphite materials. <i>Carbon</i> , 2013, 52, 49-55.	5.4	12
143	In situ purification to eliminate the influence of impurities in solution-processed organic crystals for transistor arrays. <i>Journal of Materials Chemistry C</i> , 2013, 1, 1352-1358.	2.7	37
144	Conduction Tuning of Graphene Based on Defect-Induced Localization. <i>ACS Nano</i> , 2013, 7, 5694-5700.	7.3	78

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145	Contact Thickness Effects in Bottom-Contact Coplanar Organic Field-Effect Transistors. IEEE Electron Device Letters, 2013, 34, 535-537.	2.2	13
146	How small the contacts could be optimal for nanoscale organic transistors?. Organic Electronics, 2013, 14, 1797-1804.	1.4	16
147	Effects of dopants in InOx-based amorphous oxide semiconductors for thin-film transistor applications. Applied Physics Letters, 2013, 103, .	1.5	103
148	Joule's law for organic transistors exploration: Case of contact resistance. Journal of Applied Physics, 2013, 113, 064507.	1.1	19
149	Thin-film transistors fabricated by low-temperature process based on Ga- and Zn-free amorphous oxide semiconductor. Applied Physics Letters, 2013, 102, .	1.5	59
150	Current on/off operation of graphene transistor with dual gates and He ion irradiated channel. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1608-1611.	0.8	5
151	Flexible field-effect transistor arrays with patterned solution-processed organic crystals. AIP Advances, 2013, 3, .	0.6	19
152	Surface Selectively Deposited Organic Single-crystal Transistor Arrays with High Device Performance. Molecular Crystals and Liquid Crystals, 2012, 566, 13-17.	0.4	4
153	Metal-diffusion-induced ITO nanoparticles at the organic/ITO interface. Journal Physics D: Applied Physics, 2012, 45, 165104.	1.3	3
154	Charge trapping at organic/self-assembly molecule interfaces studied by electrical switching behaviour in a crosspoint structure. Journal Physics D: Applied Physics, 2012, 45, 025304.	1.3	1
155	Control of neural signal propagation in neuron by three terminal electrodes method. Electronics Letters, 2012, 48, 1093-1095.	0.5	0
156	Temperature dependence of frequency response characteristics in organic field-effect transistors. Applied Physics Letters, 2012, 100, 183308.	1.5	10
157	Highly enhanced charge injection in thienoacene-based organic field-effect transistors with chemically doped contact. Applied Physics Letters, 2012, 100, .	1.5	130
158	Reduction of charge injection barrier by 1-nm contact oxide interlayer in organic field effect transistors. Applied Physics Letters, 2012, 100, .	1.5	37
159	Role of atomic terraces and steps in the electron transport properties of epitaxial graphene grown on SiC. AIP Advances, 2012, 2, .	0.6	21
160	Gate-Controlled P _n -N Junction Switching Device with Graphene Nanoribbon. Applied Physics Express, 2012, 5, 015101.	1.1	17
161	Single-Crystalline Nanogap Electrodes: Enhancing the Nanowire-Breakdown Process with a Gaseous Environment. ACS Applied Materials & Interfaces, 2012, 4, 5542-5546.	4.0	14
162	Direct formation of organic semiconducting single crystals by solvent vapor annealing on a polymer base film. Journal of Materials Chemistry, 2012, 22, 8462.	6.7	55

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